

Process Details

Wafer Size	5"
PDPW(pcs/Wafer)	10860 pcs/wafer
Chip Size(La)	1000um*1000um
Pad size(Lb)	830um*830um
Die Thickness	250±20um
Top Side Metalization	Ag:3.0um
Back Side Metalization	Ag: 1.5um
Passivation layer	SiO ₂ :1.0um
Street Size	50um



Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified)

Item	Symbol	Value	Unit
Operating Temperature	T _J	175	°C
Storage Temperature	T _{STG}	-30 to +150	°C

Electrical Characteristics ((Rating at 25°C ambient temperature unless otherwise specified))

Part No.	V _Z (V)	@I _{ZT} =mA	Z _{ZK} (Ω) @I _{ZK} =1mA	Z _{ZT} (Ω)	@I _{ZT} =mA A	I _R (uA)	V _R (V)
			Max.	Max.		Max.	
GDZ2CW100068YY-CS	6.46~7.14	175	200	1	175	150	5.2